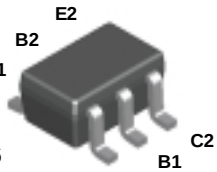
FAIRCHILD
SEMICONDUCTOR TM

BC847S



SC70-6
Mark: 1C

NOTE: The pinouts are symmetrical; pin 1 and pin 4 are interchangeable. Units inside the carrier can be of either orientation and will not affect the functionality of the device.

NPN Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 200 mA. Sourced from Process 07.

Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V_{CES}	Collector-Base Voltage	50	V
V_{CBO}	Collector-Base Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BC847S	
P_D	Total Device Dissipation Derate above 25°C	300 2.4	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	°C/W

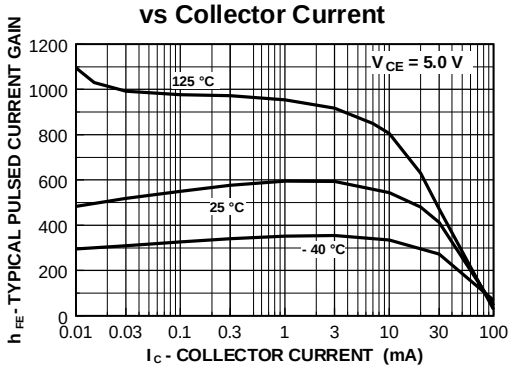
NPN Multi-Chip General Purpose Amplifier
(continued)

Electrical Characteristics
T_A = 25°C unless otherwise noted

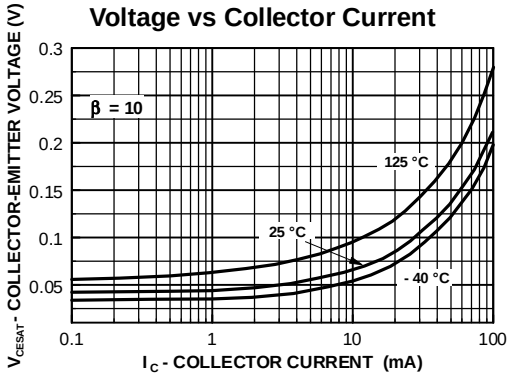
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C = 10 mA, I_B = 0	45			V
$V_{(BR)CES}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 µA, I_C = 0	6.0			V
I_{CBO}	Collector-Cutoff Current	V_{CB} = 30 V, I_E = 0 V_{CB} = 30 V, I_E = 0, T_A = 150°C			15 5.0	nA µA
ON CHARACTERISTICS						
h_{FE}	DC Current Gain	I_C = 2.0 mA, V_{CE} = 5.0 V	110		630	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 10 mA, I_B = 0.5 mA I_C = 100 mA, I_B = 5.0 mA			0.25 0.65	V V
$V_{BE(on)}$	Base-Emitter ON Voltage	I_C = 2.0 mA, V_{CE} = 5.0 V I_C = 10 mA, V_{CE} = 5.0 V	0.58		0.7 0.77	V V
SMALL SIGNAL CHARACTERISTICS						
f_T	Current Gain - Bandwidth Product	I_C = 20 mA, V_{CE} = 5.0, f = 100 mHz		200		MHz
C_{obo}	Output Capacitance	V_{CB} = 10 V, f = 1.0 MHz		2.0		pF

Typical Characteristics

Typical Pulsed Current Gain vs Collector Current



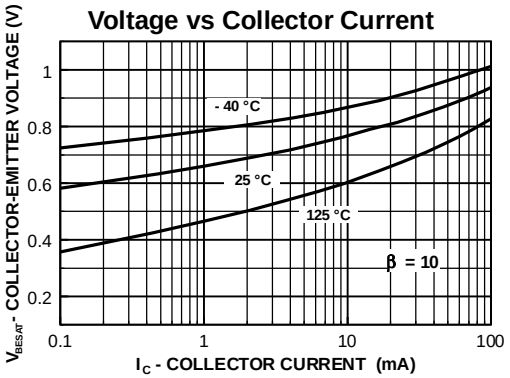
Collector-Emitter Saturation Voltage vs Collector Current



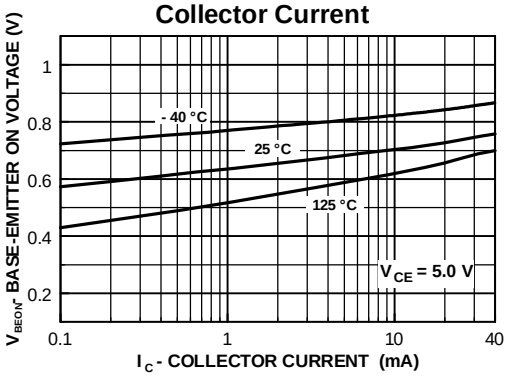
NPN Multi-Chip General Purpose Amplifier
(continued)

Typical Characteristics

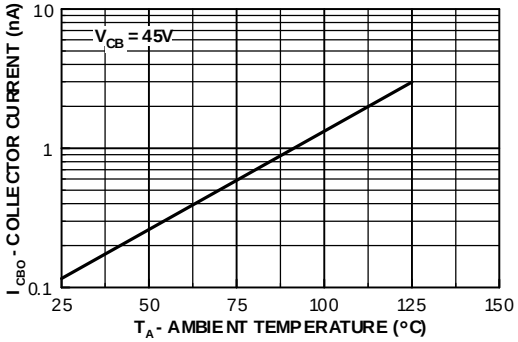
Base-Emitter Saturation Voltage vs Collector Current



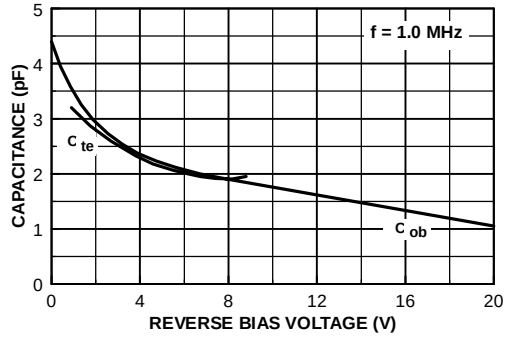
Base-Emitter ON Voltage vs Collector Current



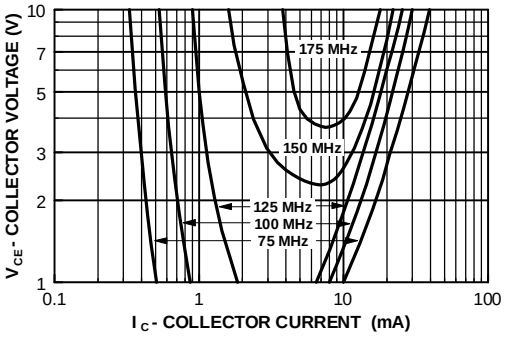
Collector-Cutoff Current vs Ambient Temperature



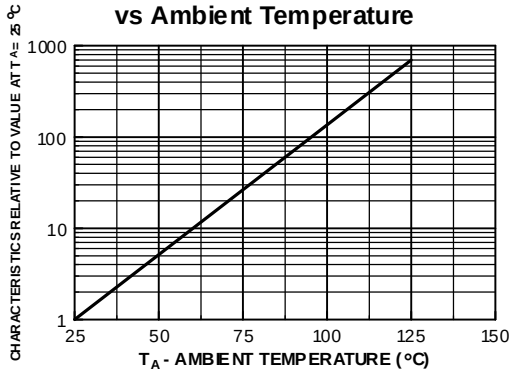
Input and Output Capacitance vs Reverse Bias Voltage



Contours of Constant Gain Bandwidth Product (f_T)

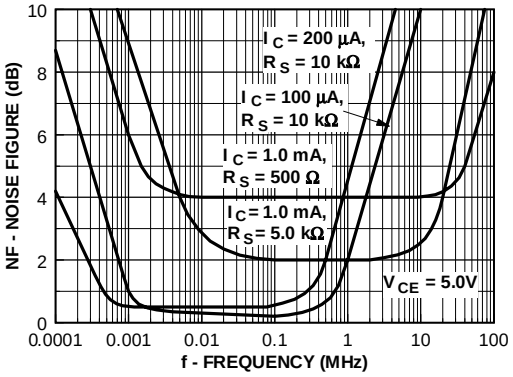


Normalized Collector-Cutoff Current vs Ambient Temperature

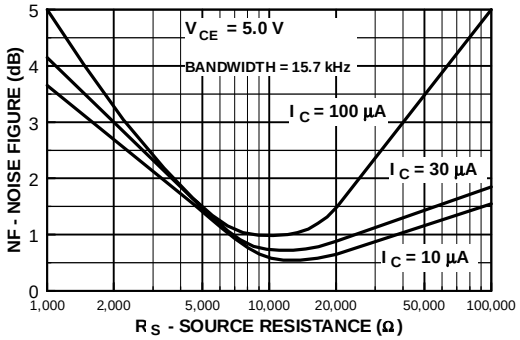


Typical Characteristics (continued)

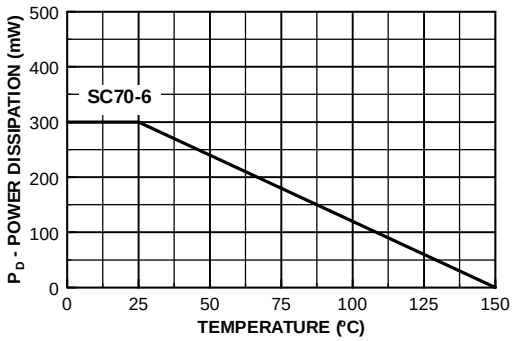
Noise Figure vs Frequency



Wideband Noise Frequency vs Source Resistance



Power Dissipation vs Ambient Temperature



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FAST®	OPTOLOGIC™	SMART START™	VCX™
Bottomless™	FASTr™	OPTOPLANAR™	STAR*POWER™	
CoolFET™	FRFET™	PACMAN™	Stealth™	
CROSSVOLT™	GlobalOptoisolator™	POP™	SuperSOT™-3	
DenseTrench™	GTO™	Power247™	SuperSOT™-6	
DOME™	HiSeC™	PowerTrench®	SuperSOT™-8	
EcoSPARK™	ISOPLANAR™	QFET™	SyncFET™	
E^2CMOS™	LittleFET™	QS™	TruTranslation™	
EnSigna™	MicroFET™	QT Optoelectronics™	TinyLogic™	
FACT™	MicroPak™	Quiet Series™	UHC™	
FACT Quiet Series™	MICROWIRE™	SLIENT SWITCHER®	UltraFET®	

STAR*POWER is used under license

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.